

BC856BM3T5G

Preferred Devices

General Purpose Transistor

PNP Silicon

This transistor is designed for general purpose amplifier applications. It is housed in the SOT-723 which is designed for low power surface mount applications.

- This is a Pb-Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-65	V
Collector-Base Voltage	V_{CBO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	265	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	470	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	640	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	195	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

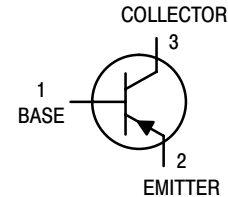
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

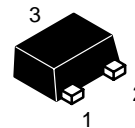


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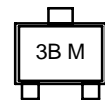
<http://onsemi.com>



MARKING DIAGRAM



SOT-723
CASE 631AA
STYLE 1



3B = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
BC856BM3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I _C = –10 mA)	V _{(BR)CEO}	–65	–	–	V
Collector–Emitter Breakdown Voltage (I _C = –10 μA, V _{EB} = 0)	V _{(BR)CES}	–80	–	–	V
Collector–Base Breakdown Voltage (I _C = –10 μA)	V _{(BR)CBO}	–80	–	–	V
Emitter–Base Breakdown Voltage (I _E = –1.0 μA)	V _{(BR)EBO}	–5.0	–	–	V
Collector Cutoff Current (V _{CB} = –30 V) (V _{CB} = –30 V, T _A = 150°C)	I _{CBO}	–	–	–15 –4.0	nA μA

ON CHARACTERISTICS

DC Current Gain (I _C = –10 μA, V _{CE} = –5.0 V) (I _C = –2.0 mA, V _{CE} = –5.0 V)	h _{FE}	– 220	150 290	– 475	–
Collector–Emitter Saturation Voltage (I _C = –10 mA, I _B = –0.5 mA) (I _C = –100 mA, I _B = –5.0 mA)	V _{CE(sat)}	– –	– –	–0.3 –0.65	V
Base–Emitter Saturation Voltage (I _C = –10 mA, I _B = –0.5 mA) (I _C = –100 mA, I _B = –5.0 mA)	V _{BE(sat)}	– –	–0.7 –0.9	– –	V
Base–Emitter Voltage (I _C = –2.0 mA, V _{CE} = –5.0 V) (I _C = –10 mA, V _{CE} = –5.0 V)	V _{BE(on)}	–0.6 –	– –	–0.75 –0.82	mV

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I _C = –10 mA, V _{CE} = –5.0 Vdc, f = 100 MHz)	f _T	100	–	–	MHz
Output Capacitance (V _{CB} = –10 V, f = 1.0 MHz)	C _{obo}	–	–	4.5	pF
Noise Figure (I _C = –0.2 mA, V _{CE} = –5.0 Vdc, R _S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	–	10	dB

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TYPICAL CHARACTERISTICS

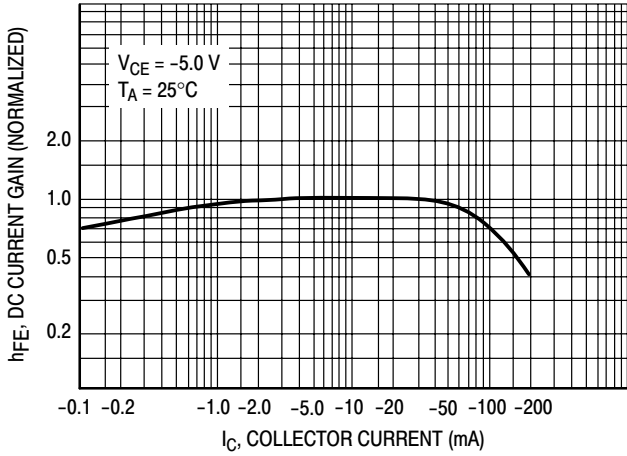


Figure 1. DC Current Gain

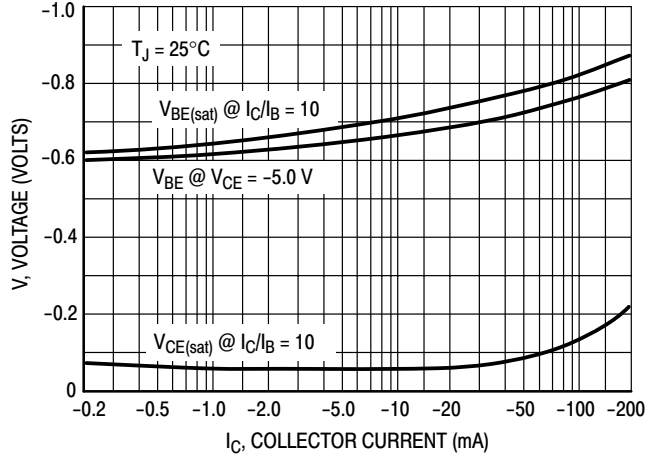


Figure 2. "On" Voltage

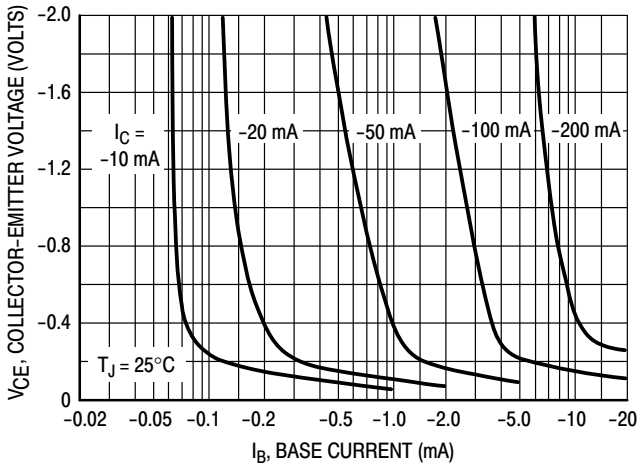


Figure 3. Collector Saturation Region

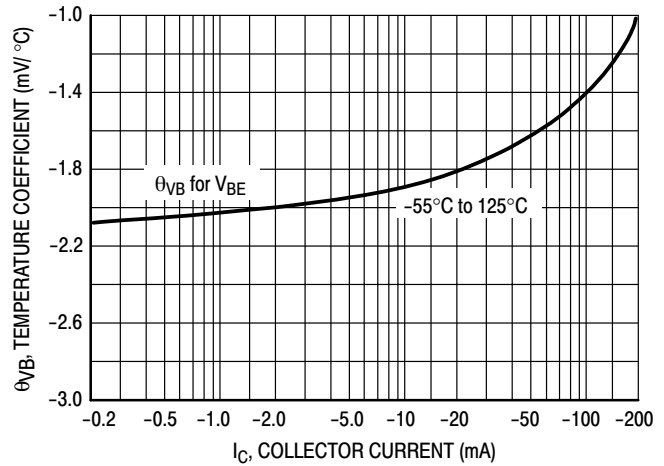


Figure 4. Base-Emitter Temperature Coefficient

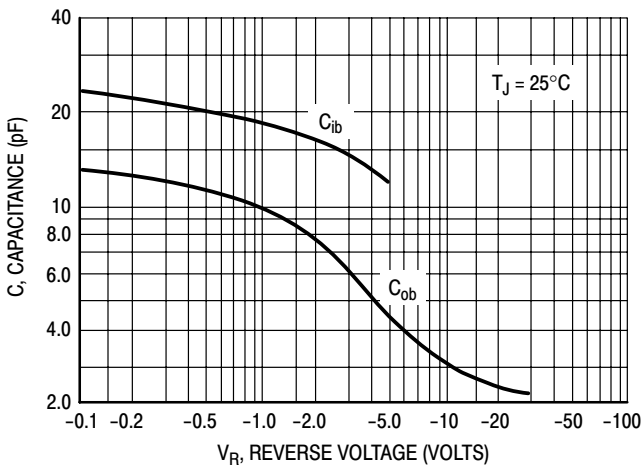


Figure 5. Capacitance

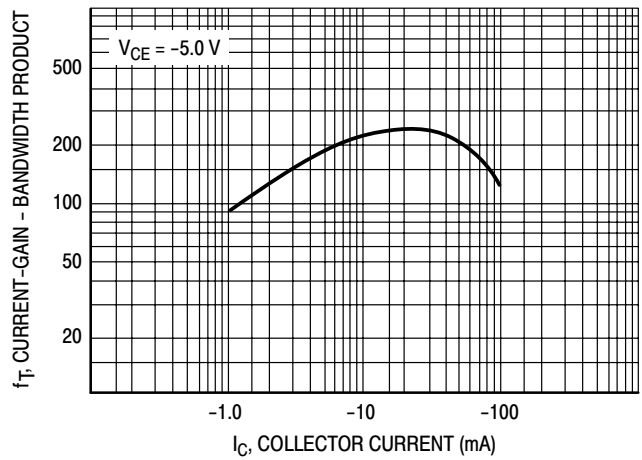


Figure 6. Current-Gain - Bandwidth Product

